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Transmitted herewith for filing is the Patent Application of:

Inventor: MIN-HSIUNG CHIANG, JIN-YUAN LEE AND JENN MING HUANG

For: METHOD FOR FORMING HIGH PURITY SILICON OXIDE FIELD OXIDE ISOLATION REGION

JC586 U.S. PTO

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Enclosed are:

06/04/99

 $\mathbf{x}$  1 sheets of drawing(s) - formal.

An assignment of the invention to Taiwan Semiconductor Manufacturing Company

An associate power of attorney

The filing fee has been calculated as shown below:

	(Col. 1)	(Col. 2)	OTHER THAN A	SMALL ENTITY	
FOR:	NO. FILED	NO. EXTRA	RATE	FEE	
BASIC FEE				\$ 760.	
TOTAL CLAIMS	<b>10</b> -20=	0	x 18 =	\$ 0.	
INDEP CLAIMS	<b>2</b> -3=	0	x 78 =	\$ 0.	
MULTIPLE	+ 260 =				
Control (Control	<b>\$</b> 760.				
		A	SSIGNMENT	\$40.	
		L	OTAL	\$ 800.	

Please charge my Deposit Account No. 19-0033 in the amount of \$ 800. A duplicate copy of this sheet is enclosed.

The Commissioner is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account No. 19-0033. A duplicate copy of this sheet is enclosed.

x Any additional filing fees required under 37 CFR \$1.16.

 $\mathbf{x}$  Any patent application processing fees under 37 CFR §1.17.

Respectfully submitted,

STEPHEN B. ACKERMAN, REG. NO. 37,761

14902 U.S. PTO 09/325951

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¥ ;	MIN-HSIUNG CHIANG, TAIPEI, TAIWAN; JIN-YUAN LEE, HSIN-CHU, TAIWAN; JENN-MING HUANG, HSIN-CHU, TAIWAN.								
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